

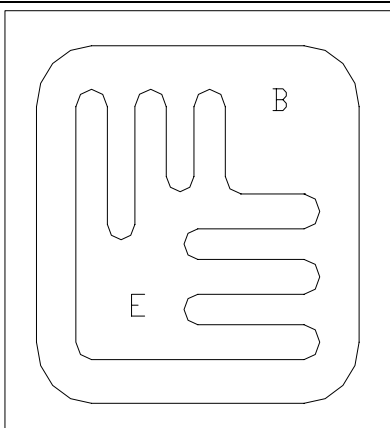
5551 Silicon NPN Epitaxial Transistor

Description: The 5551 is designed for general purpose applications requiring high breakdown voltage

Features: ●High collector-emitter breakdown voltage ($V_{CEO} \geq 160V @ I_C = 1mA$)

●Complementary to 5401

Chip Appearance

	Chip Size		440um × 440um
	Chip Thickness		210 ± 20um
	Bonding Pad Size	Base	110um × 110um
		Emitter	110um × 110um
	Front Metal		Al/AlSiCu
	Backside Metal		Au
	Wafer Size		6 inch

Electrical Characteristics($T_a = 25^\circ C$)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 120V, I_E = 0$		100	nA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 4V, I_C = 0$		100	nA
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C = 0.1mA$	180		V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C = 1mA$	160		V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E = 0.1mA$	5.0		V
DC Current Gain	h_{FE}	$V_{CE} = 5V, I_C = 10mA$	80	400	
Collector Saturation Voltage	$V_{CE(sat)}$	$I_C = 10mA, I_B = 1mA$		0.2	V